Oral presentation | 15 Crystal Engineering | 15.6 Group IV Compound Semiconductors (SiC)

[10p-Z23-1~16]15.6 Group IV Compound Semiconductors (SiC)

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Thu. Sep 10, 2020 1:15 PM - 6:00 PM Z23

△：Presentation by Applicant for JSAP Young Scientists Presentation Award

▲：English Presentation

▼：Both of Above

No Mark：None of Above

3:45 PM - 4:00 PM

[10p-Z23-9][The 42nd JSAP Young Scientist Award Speech] Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p– i– n diodes

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Keywords:SiC, stacking fault, basal plane dislocation

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